

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-3. (Canceled)

4. (Currently Amended) A semiconductor device comprising:

~~a support which is an adhesive material~~ substrate;

an adhesive material over the substrate;

a protective film over the support adhesive material;

an insulating film over the protective film; and

a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film,

wherein the middle processing component includes a thin film transistor of n-channel type and a thin film transistor of p-channel type.

5. (Currently Amended) A semiconductor device according to ~~any one of claims 1, 2, or 4~~ claim 4, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.

6.-19. (Canceled)

20. (Currently Amended) A semiconductor device comprising:

~~a first protective film~~ a substrate;

~~a thin film transistor over the first protective film~~;

~~a support which is an adhesive material over the thin film transistor substrate;~~  
and  
~~a second protective film over the support adhesive material;~~  
~~an insulating film over the protective film;~~  
~~a middle processing component comprising a control section and an operation~~  
~~section, and a memory unit over the insulating film; and~~  
~~a battery over the substrate;~~  
~~wherein the middle processing component includes a thin film transistor of n-~~  
~~channel type and a thin film transistor of p-channel type.~~

21.-27. (Canceled)

28. (New) A semiconductor device comprising:  
a plastic substrate;  
an adhesive material over the plastic substrate; and  
a protective film over the adhesive material, said protective film comprising a material selected from the group consisting of SnO<sub>2</sub>, SrO, Teflon, and metal;  
an insulating film over the protective film, said insulating film comprising silicon oxynitride;  
a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film; and  
a battery over the plastic substrate;  
wherein the middle processing component includes a thin film transistor of n-channel type and a thin film transistor of p-channel type.

29. (New) A semiconductor device comprising:

a plastic substrate;  
an adhesive material over the plastic substrate; and

a protective film over the adhesive material, said protective film comprising a material selected from the group consisting of SnO<sub>2</sub>, SrO, Teflon, and metal;  
an insulating film over the protective film;  
a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film; and  
wherein the middle processing component includes a thin film transistor of n-channel type and a thin film transistor of p-channel type.

30. (New) A semiconductor device according to claim 28, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.

31. (New) A semiconductor device according to claim 29, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.